Form PTO-1449 (REV. 2-32) U.S. Department of Commerce Patent and Trademark Office	Atty. Docket No. A110-US	Serial No. 09/800,213
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant John H. Coleman	
	Filing Date March 6, 2001	Group 2826

U.S. PATENT DOCUMENTS

*Exam. Init.		Document No.	Date	Name	Class	Subclass	Filing Date if Appropriate
MLT		5,191,371	03-30-93	Li	437	11	
MLT		5,633,174	05-27-97	Li	438	475	
MLT		5,034,343	07-23-91	Rouse et al.	437	86	
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MLT		6,144,070	11-7-00	Iwamatsu et al.	257	347	1-15-99

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		Document No.	Date	Country	Class	SubClass	Translator Yes	Translator No

OTHER DOCUMENTS (including Author, Title Date, Pertinent Pages, Etc.)

MLT			Jianming Li et al., Properties of Silicon-on-Defect-Layer Material, in: Materials Research Society Symposium Proceedings Vol. 396, David B. Poker et al., Ed., pp.745-750
MLT			Jianming Li, New annealing processes and explanation for novel silicon pn junctions formed by proton implantation, Electronics Letters, Vol. 35 (1997), pp. 133-134

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* Examiner: Initial citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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MLT			Jianming Li et al., Properties of proton-implanted p-type Si: supports for the model explaining a novel p-n junction in Si, Nuclear Instruments and Methods in Physics Research B 160 (2000), pp. 190-193
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